

## Silicon NPN Power Transistors

2SC3264

## DESCRIPTION

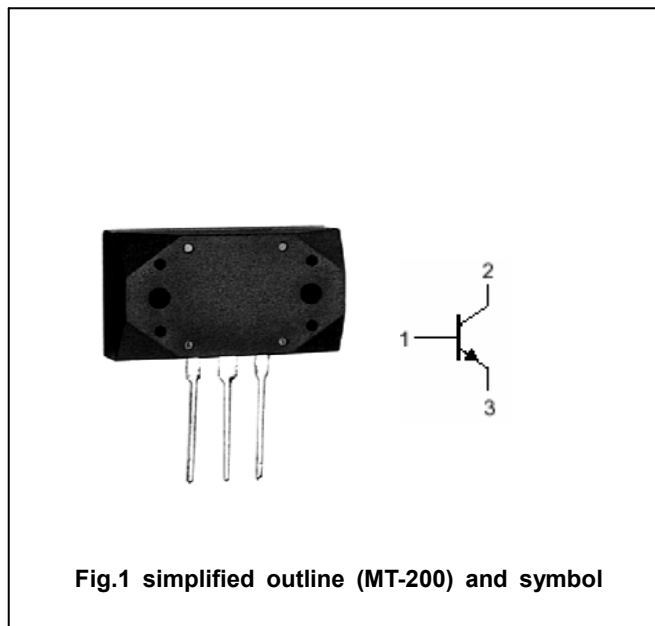
- With MT-200 package
- Complement to type 2SA1295

## APPLICATIONS

- Audio and general purpose applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_a=25^\circ$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	230	V
$V_{CEO}$	Collector-emitter voltage	Open base	230	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		17	A
$I_B$	Base current		5	A
$P_C$	Collector power dissipation	$T_C=25^\circ$	200	W
$T_j$	Junction temperature		150	$^\circ$
$T_{stg}$	Storage temperature		-55~150	$^\circ$

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## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA$ ; $I_B=0$	230			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=5A$ ; $I_B=0.5A$			2.0	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=230V$ ; $I_E=0$			100	$\mu A$
$I_{EBO}$	Emitter cut-off current	$V_{EB}=5V$ ; $I_C=0$			100	$\mu A$
$h_{FE}$	DC current gain	$I_C=5A$ ; $V_{CE}=4V$	50		140	
$C_{ob}$	Output capacitance	$I_E=0$ ; $V_{CB}=10V$ ; $f=1MHz$		250		pF
$f_T$	Transition frequency	$I_E=-2A$ ; $V_{CE}=12V$		60		MHz

## Switching times

$t_{on}$	Turn-on time	$I_C=5A$ ; $R_L=12\Omega$ $I_{B1}=-I_{B2}=0.5A$ $V_{CC}=60V$		0.30		$\mu s$
$t_s$	Storage time			2.40		$\mu s$
$t_f$	Fall time			0.50		$\mu s$

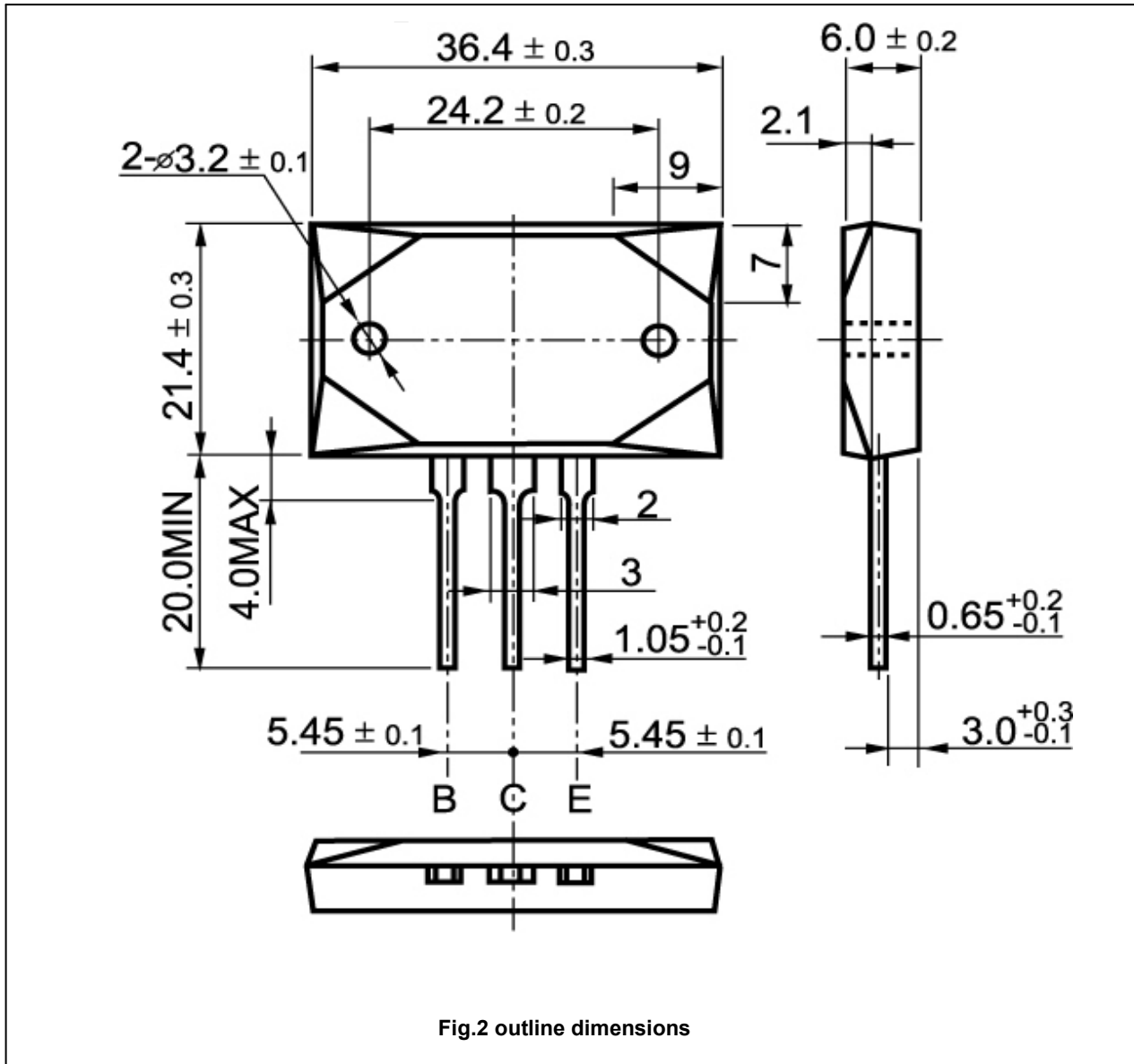
◆  $h_{FE}$  classifications

O	Y
50-100	70-140

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PACKAGE OUTLINE



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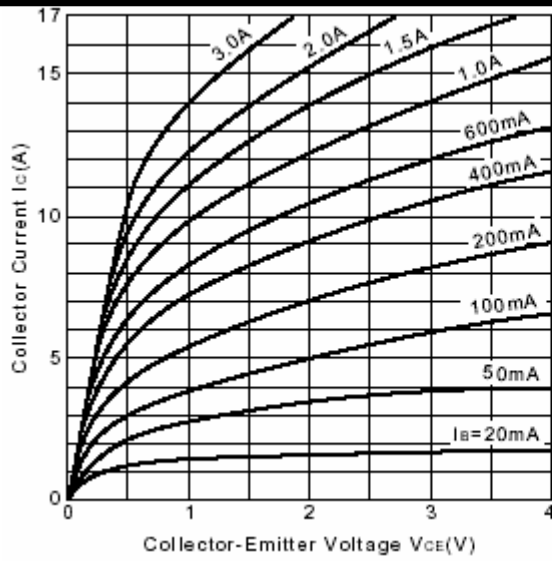


Fig.3 Static Characteristic

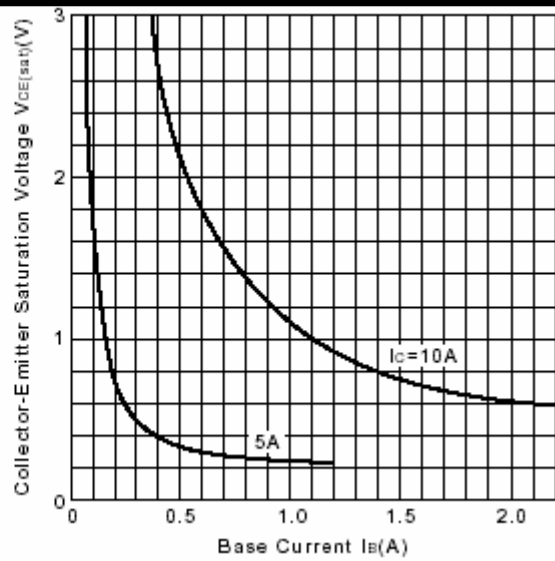


Fig.4  $V_{CE(sat)}-I_B$

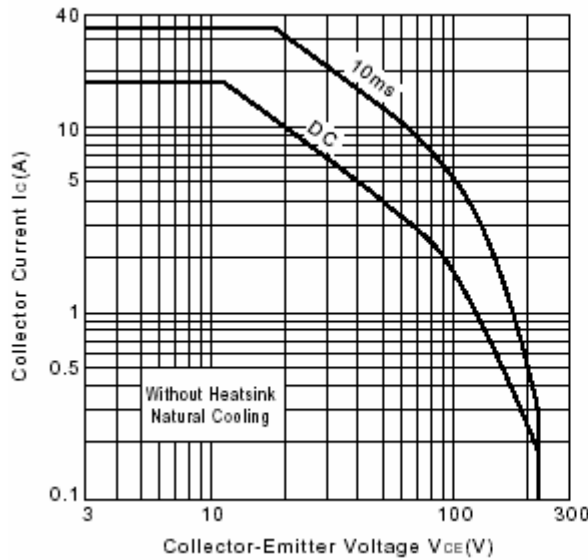


Fig.5 Safe Operating Area

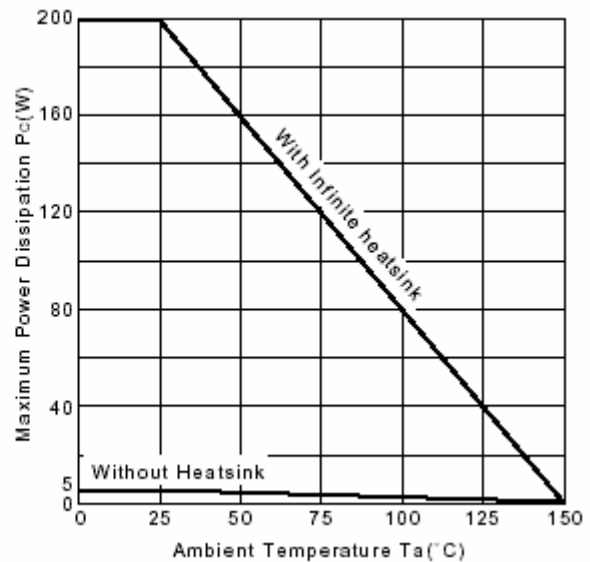


Fig.6 Power Derating

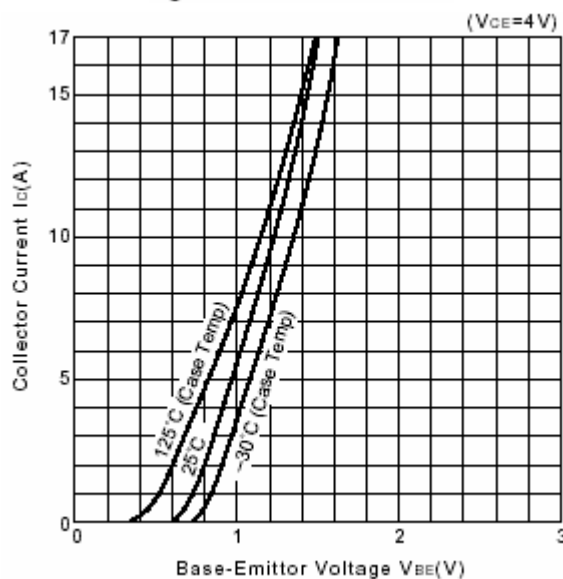


Fig.7  $I_C-V_{BE}$

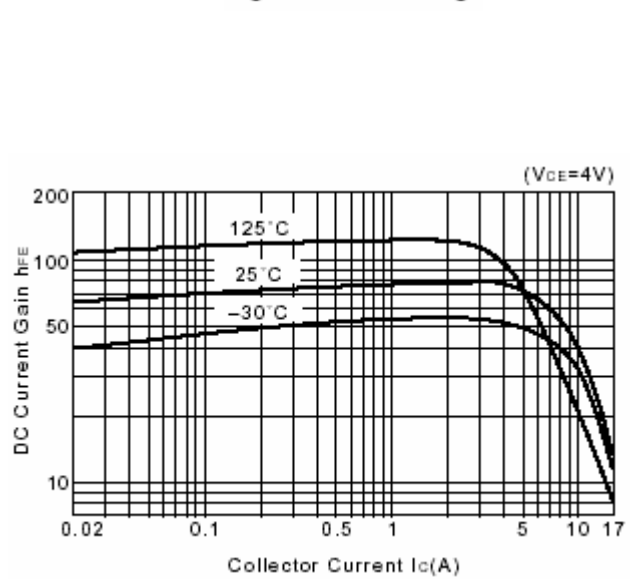


Fig.8 DC current Gain